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برای کسب اطلاعات بیشتر بر روی لینک ها کلیک کنید

- 7 سال سابقه آموزش تعمیرات تخصصی دستگاه های جوش اینورتری تک فاز و 3 فاز
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  - آموزش تخصصی ابراز آلات شارژی

# ONSEMA NPN General-Purpose Amplifier

# 2N5551

## Description

This device is designed for general-purpose high-voltage amplifiers and gas discharge display drivers.

### Features

• These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### ABSOLUTE MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Value	Unit
V <sub>CEO</sub>	Collector-Emitter Voltage	160	V
V <sub>CBO</sub>	Collector-Base Voltage	180	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
lc	Collector Current - Continuous	600	mA
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature (Note 2)	-55 to + 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.
- These ratings are based on a maximum junction temperature of 150°C. These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty cycle operations.



### MARKING DIAGRAM



#### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 5.

# 2N5551

#### THERMAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted) (Note 3)

Symbol	Characteristic	Мах	Unit
PD	Total Device Dissipation	625	mW
	Derate Above 25°C	5.0	mW/°C
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	83.3	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W

#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted) (Note 4)

Symbol	Parameter	Test Conditions	Min	Max	Unit
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1.0 mA, I <sub>B</sub> = 0	160		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 100 μA, I <sub>E</sub> = 0	180		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10 μA, I <sub>C</sub> = 0	6.0		V
I <sub>CBO</sub>	Collector Cut-Off Current	V <sub>CB</sub> = 120 V, I <sub>E</sub> = 0		50	nA
		V <sub>CB</sub> = 120 V, I <sub>E</sub> = 0 V, T <sub>A</sub> = 100° C		50	μA
I <sub>EBO</sub>	Emitter Cut-Off Current	V <sub>EB</sub> = 4.0 V, I <sub>C</sub> = 0		50	nA

#### **ON CHARACTERISTICS**

h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 5.0 V	80		
		I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 V	80	250	
		$I_{C}$ = 10 mA, $V_{CE}$ = 5.0 V (for 2N5551YBU, 2N5551YTA)	180	240	
		I <sub>C</sub> = 50 mA, V <sub>CE</sub> = 5.0 V	30		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1.0 mA		0.15	V
		I <sub>C</sub> = 50 mA, I <sub>B</sub> = 5.0 mA		0.20	V
V <sub>BE(sat)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1.0 mA		1.0	V
		I <sub>C</sub> = 50 mA, I <sub>B</sub> = 5.0 mA		1.0	V

# SMALL-SIGNAL CHARACTERISTICS

fT	Current Gain Bandwidth Product	$I_{C}$ = 10 mA, $V_{CE}$ = 10 V, f = 100 MHz	100		MHz
C <sub>obo</sub>	Output Capacitance	$V_{CB}$ = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz		6.0	pF
C <sub>ibo</sub>	Input Capacitance	$V_{BE}$ = 0.5 V, I <sub>C</sub> = 0, f = 1.0 MHz		20	pF
H <sub>fe</sub>	Small-Signal Current Gain	$I_{C}$ = 1.0 mA, $V_{CE}$ = 10 V, f = 1.0 kHz	50	250	
NF	Noise Figure	I <sub>C</sub> = 250 μA, V <sub>CE</sub> = 5.0 V, R <sub>S</sub> = 1.0 kΩ, f = 10 Hz to 15.7 kHz		8.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. PCB board size FR-4 76 x 114 x 0.6 T mm<sup>3</sup> (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

4. Pulse test: pulse width  $\leq$  300 µs, duty cycle  $\leq$  2.0%.

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# **TYPICAL PERFORMANCE CHARACTERISTICS**







Figure 3. Base–Emitter Saturation Voltage

vs. Collector Current





Figure 2. Collector – Emitter Saturation Voltage vs. Collector Current



I<sub>C</sub>, Collector Current (mA)

Figure 4. Base–Emitter On Voltage vs. Collector Current



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# TYPICAL PERFORMANCE CHARACTERISTICS (CONTINUED)



Figure 7. Collector–Emitter Breakdown Voltage with Resistance between Emitter–Base



Figure 9. Power Dissipation vs. Ambient Temperature



Figure 8. Small Signal Current Gain vs. Collector Current

## **ORDERING INFORMATION (Note 5)**

Part Number	Top Mark	Package	Shipping <sup>†</sup>
2N5551TA	5551	TO-92-3, Case 135AR (Pb-Free)	2000 / Ammo Pack
2N5551TFR	5551	TO-92-3, Case 135AR (Pb-Free)	2000 / Tape & Reel
2N5551TF	5551	TO-92-3, Case 135AR (Pb-Free)	2000 / Tape & Reel
2N5551BU	5551	TO-92-3, Case 135AN (Pb-Free)	10000 / Bulk Bag
2N5551YBU	5551Y	TO-92-3, Case 135AN (Pb-Free)	10000 / Bulk Bag

# DISCONTINUED (Note 6)

2N5551CTA	5551	TO-92-3, Case 135AR (Pb-Free)	2000 / Ammo Pack
2N5551YTA	5551Y	TO-92-3, Case 135AR (Pb-Free)	2000 / Ammo Pack

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
5. Suffix "-Y" means h<sub>FE</sub> 180~240 in 2N5551 (Test condition: I<sub>C</sub> = 10 mA, V<sub>CE</sub> = 5.0 V)
6. **DISCONTINUED**: These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on <u>www.onsemi.com</u>.

# onsemi

TO-92 3 4.825x4.76 CASE 135AN ISSUE O DATE 31 JUL 2016 5.20 4.32 5.33 4.32 (0.81) 15.62 13.20 2 3 0.52 0.56 0.36 1.27 NOTES: UNLESS OTHERWISE SPECIFIED 2.54 DRAWING WITH REFERENCE TO JEDEC TO-92 A) RECOMMENDATIONS. B) ALL DIMENSIONS ARE IN MILLIMETERS. c) DRAWING CONFORMS TO ASME Y14.5M-2009. 4.19 3.05 2.66 2.13 2 3 1 Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. **DOCUMENT NUMBER:** 98AON13880G **DESCRIPTION:** TO-92 3 4.825X4.76 PAGE 1 OF 1 onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.



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